

Practical Interpretation of LET Requirements

Saab Space



Stanley Mattsson

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SEE Requirements from Alcatel Alenia Space

❑ Pragmatic and “in principal” easy to comply to.

❑ Destructive SEE:

➤ $LET \geq 60 \text{ MeV /cm}^2/\text{mg}$ & 10^7 ions/cm^2 : No Events Observed

✓ $LET \geq 60$ approximated with Xe \Rightarrow Frequently available beams, No tilting required

✓ 10^7 ions/cm^2 : @ Xe \Rightarrow Usually no problem with use of high ion FLUX

✓ 1000 - 3000 ions/sec \Rightarrow 3h – 1h beam time

❑ Non-Destructive SEE:

➤ Ions & Energies shall be selected in order to make sure that

✓ Saturated device cross section is obtained

✓ Ion range greater than EPI layer thickness (valid for destructive & non-destructive)

✓ Opens up for use of test data from IPN / Orsay or BNL / Brookhaven

❑ Heavy ion testing in accordance with ESA 25100 or JEDEC #57

ESA/SCC 25100

- ❑ Test & Bias Conditions \Rightarrow Shall be given by the test report
 - Alcatel Alenia Space: \Rightarrow Refers to ESA/SCC 25100
 - Astrium requirement: \Rightarrow “Typical conditions of use for application”

- ❑ Ion Range \Rightarrow Typically 30 μ m

- ❑ Ion Flux \Rightarrow Meaningful number of upsets in 1 to 20 minutes
 - “No Dose Rate Effects in SEE testing”

- ❑ Max Fluence $\Rightarrow 10^7$ ions/cm²

- ❑ 8 out of 13 of pages \Rightarrow How to write Documentations

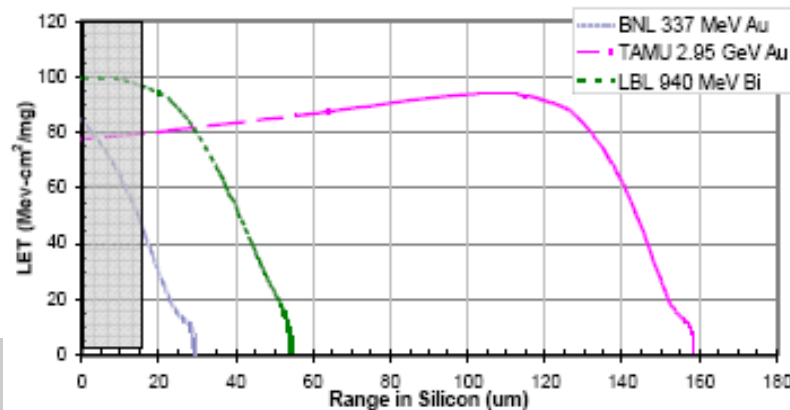
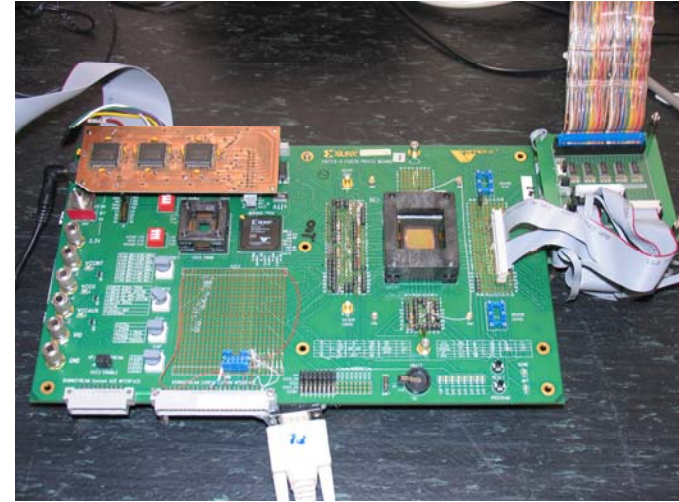
SEL Requirements General Documents

❑ No Events Observed for $LET > 70 - 110 \text{ MeV/mg/cm}^2$

- Tilt Needed for European Ion Beams
- Tilt may be difficult due to shadowing by the socket

❑ Ion Range Requirement $\Rightarrow 30\mu\text{m}$

- For Galileo, Au ions at BNL would be acceptable
 - ✓ ^{197}Au ; $LET \ 80 \text{ MeV/mg/cm}^2$, range in Si $\sim 28\mu\text{m}$
 - ✓ With $15 \mu\text{m}$ dead layer, equivalent $LET \approx 40 \text{ MeV/mg/cm}^2$ available



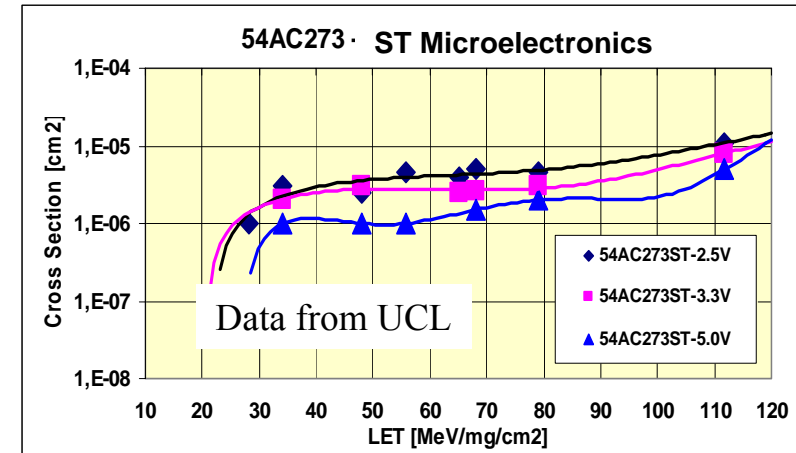
Low Ion Range

❑ Test of FF in 54AC374 from ST @ IPN

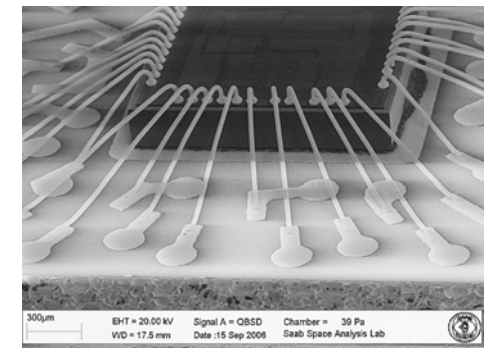
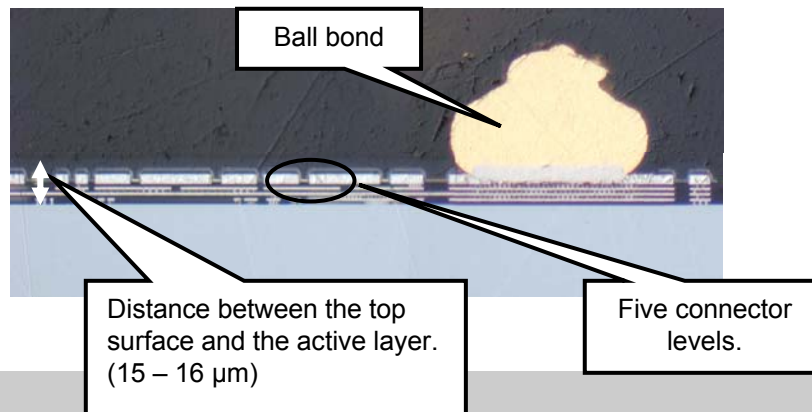
- SEU free LET ≤ 93 MeV/mg/cm² ;
 - ✓ Ion ¹²⁷I, range 30μm, tilt 48°, Fluence 1E+6
 - ✓ (10^7 ions/cm² forgotten for CNES / ESA reports)

❑ Test of FF in 54AC273 from ST @ UCL

- This could be due to range or test set-up



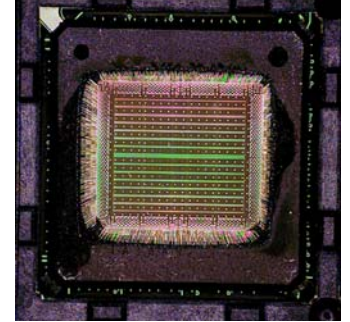
❑ Ions of short range require detailed information about DUT



SEM picture of small ASIC

Problems with High Ion Flux @ High LET Values

- ❑ Evaluation of “Commercial” Parts Not Seldom Etched Plastic Parts Tested in “Special Evaluation Campaigns”
- ❑ Device preparation delicate work
- ❑ Complex Devices Normally Requires Complex Test Boards
 - Test induced effects frequently observed
 - ✓ Problems related to charging of the device
 - ✓ “Spurious Events” due to conflict on “test board “ level / high error rate
 - ✓ Flux related double bit errors (TMR designs)
 - Hick-ups may require restart of test run
- ❑ Low flux @ high LET required
 - 10^7 ions/cm² @ 100 ions/sec \Rightarrow 24h beam time
 - Solution for Latch-up: Dedicated test and test board



LESSONS LEARNED from Xilinx

”Dead lock” events

Heavy Ions at RADEF, Finland

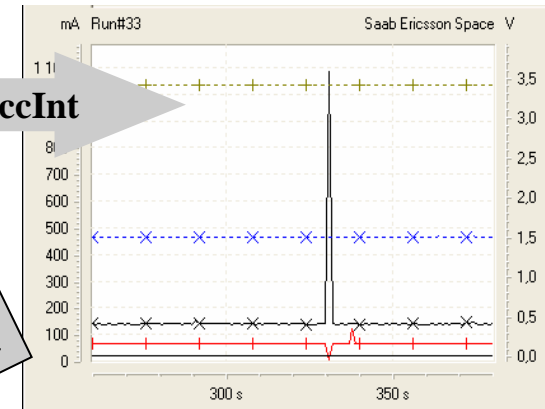
Latch-up Like Events

- Required Power
Cycling to recover test system

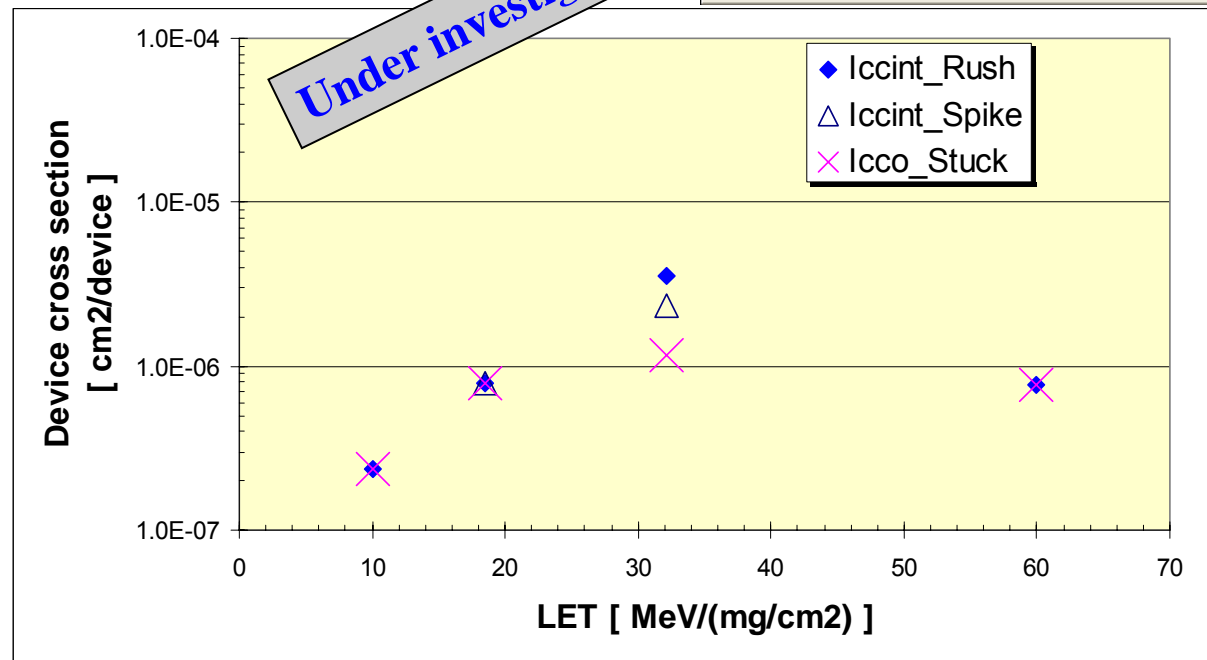
Etched plastic samples,
~ 200 out of ~700 bonds
used

Test system or circuit
problems?

>1 Amp spike on IccInt



Under investigation!



Example of Complex Device

❑ AT697E Sparc Processor from Atmel

- TMR design of Std FF in 0.18 μ technology
- Latch-up performed in separate tests to 1E+7

SEU/SET dynamic test data @100 MHz for AT697E

❑ Users are referred to Atmels data

- Heavy Ion Flux \sim 1000 ions/cm²/sec
 - ✓ Xe 5E+5 ions, errors > 10,
 - ✓ Ar, 5E+5 ions, No error

❑ Reliability aspects

- Unacceptable fluence at LET 14 (Ar)
- Flux issue; Comparing data @ lower flux needed

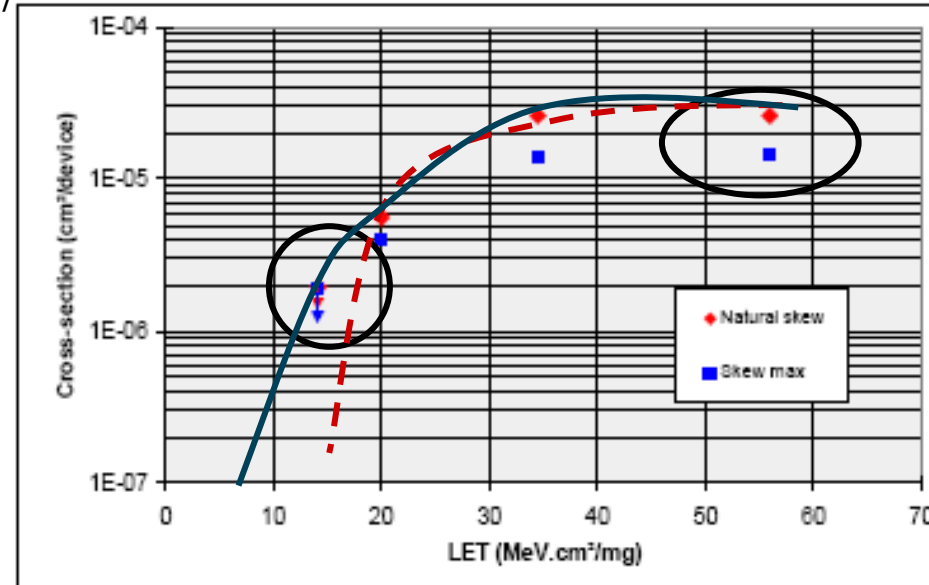


Fig. 7 : Uncorrectable errors cross sections (in cm²/device) at 100 MHz, for natural and maximum skews

Conclusions & Topics for the Round Table

- ❑ Are we rejecting / destroying useful devices by over testing ?
- ❑ For radiation analysis we have a “blunt” tool in CREME96
 - What is a realistic ratio between sensitive depth and sensitive area ($Z=X/?$)
 - Likely, we have observed test induced problems in Mosfet, SRAM, DRAM, E2prom, FlashProm, FPGA,...
 - Is high fluence testing at Xe really necessary?
 - Reliability aspects require this, but are the numbers realistic
- ❑ SEL special test @ high flux to $1E+7$
- ❑ SEU/SET tests to lower fluence

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Thank You for Your Attention